AMENDMENTS TO THE SPECIFICATION

Please replace Table 2 on page 13 with the following amended Table 2:

Table 2

	Anionic surfactant		Sulfate ion (ppm)	Methanol (% by mass)	Chloride ion (ppm)	Dimensional controllability
	Kind	Amount (ppm)				
Example 13	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	500	0.005	2000	B
Example 14	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	700	0.005	2000	B
Example 15	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	5000	0.005	2000	B
Example 16	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	700	0.05	2000	B
Example 17	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	700	0.3	2000	B
Example 18	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	700	2.5	2000	B
Example 19	C_5H_{11}-O-O-$\langle$SO_3NH_4	1000	700	0.3	300	A
Example 20	C_5H_{11}-O-O-$\langle$SO_3NH_4	1000	700	0.3	500	B
Example 21	C_5H_{11}-O-O-$\langle$SO_3NH_4	1000	700	0.005	300	B
Example 22	C_5H_{11}-O-O-$\langle$SO_3NH_4	1000	700	0.005	500	B
Example 23	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	20000	700	0.3	300	A
Example 24	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	50000	700	0.3	300	B
Example ~~22~~ 25	$C_{12}H_{25}$-O-O-$\langle$SO_3NH_4, SO_3NH_4$\rangle$	3000	700	0.3	300	B

AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A developer composition for resists, comprising an organic quaternary ammonium base as a main component, <u>said organic quaternary ammonium base having a lower alkyl group or a lower hydroxyalkyl group, wherein the lower alkyl group or lower hydroxyalkyl group has 1 to 5 carbon atoms, wherein said organic quaternary ammonium base is present in an amount from 0.1 to 10% by mass;</u>

~~said developer further comprising~~ an anionic surfactant in an amount from ~~500~~ <u>1,000</u> to ~~100,000~~ <u>50,000</u> ppm represented by the following general formula (I):
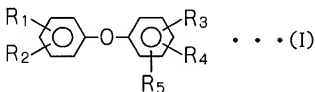
wherein at least one of R_1 and R_2 represents an alkyl or alkoxy group having 5 to ~~18~~ <u>15</u> carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to ~~18~~ <u>15</u> carbon atoms, and at least one of R_3, R_4 and R_5 represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group;

SO_4^{2-} in an amount from ~~10~~ <u>50</u> to ~~10,000~~ <u>5,000</u> ppm; and

a lower alcohol in an amount from ~~0.05~~ <u>0.005</u> to 2.5% by mass.

2. **(Canceled)**

3. **(Canceled)**

4. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

5. **(Previously presented)** The developer composition for resists according to claim 1, wherein said lower alcohol has 1 to 5 carbon atoms.

6. **(Previously presented)** The developer composition for resists according to claim 5, wherein the lower alcohol is ethanol or methanol.

7. (**Previously presented**) The developer composition for resists according to claim 1, wherein the amount of said organic quaternary ammonium base is 0.1 to 10% by mass based on the developer composition for resists.

8. (**Currently amended**) The developer composition for resists according to claim 1, further comprising a halogen ion in an amount of ~~1,000 ppm or less~~ <u>300 to 2,000 ppm</u>.

9. (**Previously presented**) The developer composition for resists according to claim 8, wherein the amount of the halogen ion is from 300 to 1,000 ppm.

10. (**New**) The developer composition for resists according to claim 1, wherein said organic quaternary ammonium base is in an amount from 2 to 5% by mass.

11. (**New**) The developer composition for resists according to claim 1, wherein said SO_4^{2-} is in an amount from 100 to 1,000 ppm.

12. (**New**) The developer composition for resists according to claim 1, wherein said lower alcohol in is in an amount from 0.1 to 1% by mass.

13. (**New**) The developer composition for resists according to claim 8, wherein said halogen ion is in an amount of 1,000 ppm or less.